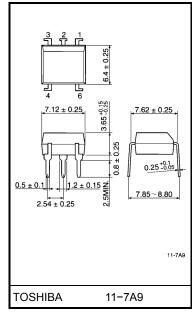
TOSHIBA Photocoupler GaAlAs Ired & Photo-Diode Array

TLP591B

Telecommunication Programmable Controllers MOS Gate Driver MOS FET Gate Driver

The TOSHIBA TLP591B consists of an aluminum galium arsenide infrared emitting diode optically coupled to a series connected photo-diode array in a six lead plastic DIP package. TLP591B is suitable for MOS FET gate driver. TLP591B has an internal shunt resistor to optimize switching speed.

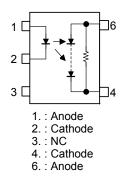
• UL recognized: UL1577, file no. E67349



Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
LED	Forward current	lF	50	mA
	Forward current derating (Ta ≥ 25°C)	∆I _F /°C	-0.5	mA /°C
	Pulse forward current (100µs pulse, 100pps)	IFP	1	А
	Reverse voltage	VR	3	V
	Junction temperature	Tj	125	°C
r	Forward current	I _{FD}	50	μA
Detector	Reverse voltage	V _{RD}	10	V
ă	Junction temperature	Tj	125	°C
Storage temperature range		T _{stg}	-55~125	°C
Operating temperature range		T _{opr}	-40~85	°C
Lead soldering temperature (10 sec.)		T _{sol}	260	°C
Isola (AC,	tion voltage , 1 min., R.H.≤ 60%) (Note 1)	BVS	2500	V _{rms}

Pin Configuration (top view)



(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together, and pins 4 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit	
Forward current	١ _F	_	20	25	mA	
Operating temperature	T _{opr}	-25		85	°C	

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	VF	I _F = 10 mA	1.2	1.4	1.7	V
LED	Reverse current	I _R	V _R = 3 V	—	—	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	60	pF
	Forward voltage	V _{FD}	I _{FD} = 10 μA	_	7	_	V
Detector	Reverse current	I _{RD}	V _{RD} = 10 V	_	7	_	μA
	Capacitance (anode to cachode)	C _{TD}	V = 0, f = 1 MHz	_	_	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Open voltage	V _{OC}	I _F = 20 mA	7	8	—	V
Short Current	Isc	I _F = 20 mA	24	40	-	μA

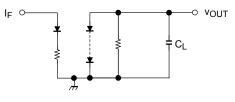
Isolation Characteristics (Ta = 25°C)

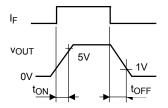
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	CS	V _S = 0, f = 1 MHz	—	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V	5×10 ¹⁰	10 ¹⁴	_	
	BVS	AC, 1 minute	2500	_	_	Vrms
Isolation voltage		AC, 1 second, in oil	—	5000	_	
		DC, 1 minute, in oil	_	5000	_	Vdc

Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Turn-on time	t _{on}	I _F = 20 mA, C _L = 1000pF	_	0.2	_	ms
Turn-off time	t _{off}	(Fig. 1)		3		ms

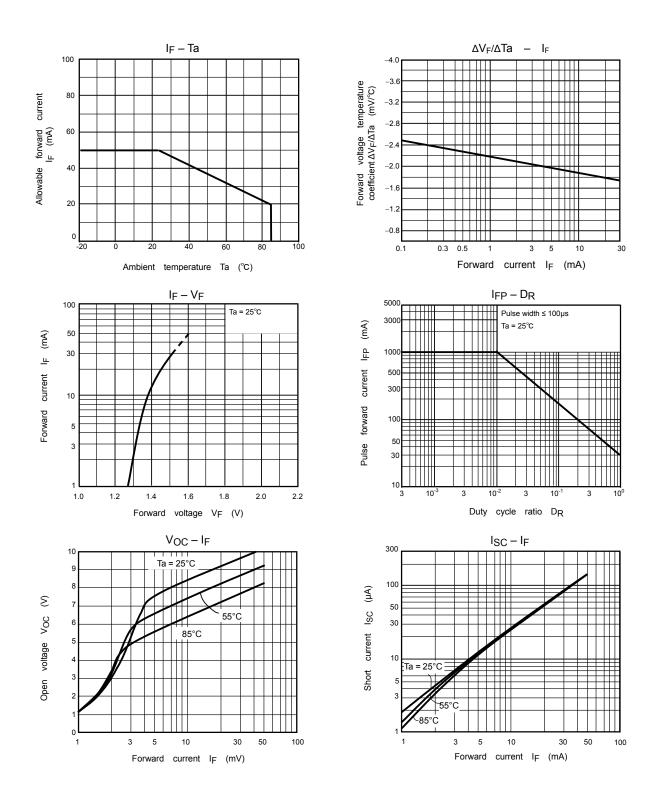
Fig. 1 Switching time test circuit





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